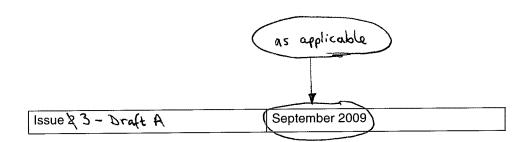


Pages 1 to 16

TRANSISTORS, LOW POWER, PNP

BASED ON TYPE 2N2894 and 2N2894A

ESCC Detail Specification No. 5202/004







as applicable

PAGE 2
ISSUE & 3 - Draft A

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PAGE 3

ISSUE & 3 - Draft A

DOCUMENTATION CHANGE NOTICE

(Refer to https://escies.org for ESCC DCR content)

DCR No.	CHANGE DESCRIPTION			
442,455	Specification up issued to incorp	orate editorial and tecl	hnical changes per DCR.	

tbd

PAGE 5

ISSUE & 3 - Draft A

1. **GENERAL**

1.1 SCOPE

This specification details the ratings, physical and electrical characteristics and test and inspection data for the component type variants and/or the range of components specified below. It supplements the requirements of, and shall be read in conjunction with, the ESCC Generic Specification listed under Applicable Documents.

1.2 APPLICABLE DOCUMENTS

The following documents form part of this specification and shall be read in conjunction with it:

- (a) ESCC Generic Specification No. 5000
- (b) MIL-STD-750, Test Methods and Procedures for Semiconductor Devices

1.3 <u>TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS</u>

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESCC Basic Specification No. 21300 shall apply.

1.4 THE ESCC COMPONENT NUMBER AND COMPONENT TYPE VARIANTS

1.4.1 The ESCC Component Number

The ESCC Component Number shall be constituted as follows:

Example: 520200401

Detail Specification Reference: 5202004

Component Type Variant Number: 01 (as required)

1.4.2 Component Type Variants

The component type variants applicable to this specification are as follows:

Variant Number	Based on Type	Case	Lead/Terminal Material and/or Finish	Weight max g
01	2N2894	TO-18	D2	0.4
02	2N28Ø4 A	TO-18	D2	0.4
03	2N2894	TO-18	D3 or D4	0.4
04	2N2894 A	TO-18	D3 or D4	0.4
05	2N2894	TO-18	D7	0.4
06	2N2894	CCP	2	0.06
07	2N2894	CCP	4	0.06

The lead/terminal material and/or finish shall be in accordance with the requirements of ESCC Basic Specification No. 23500.

PAGE 6 ISSUE & 3 - Draft A

1.5 **MAXIMUM RATINGS**

The maximum ratings shall not be exceeded at any time during use or storage.

Maximum ratings shall only be exceeded during testing to the extent specified in this specification and when stipulated in Test Methods and Procedures of the ESCC Generic Specification.

Characteristics	Symbols	Maximum Ratings	Unit	Remarks
Collector-Base Voltage	V _{CBO}	-12	V	Over entire
Collector-Emitter Voltage	V _{CEO}	-12	V	operating temperature
Emitter-Base Voltage	V _{EBO}	-4	٧	range
Collector Current	I _C	-200	mA	Continuous
Power Dissipation For TO-18 and CCP	P _{tot1}	0.36 5.58 (Note)2)	w ([At T _{amb} ≤ +25°C Note-1-
For TO-18	Ptot 2	1.2	W	At T _{case} ≤ +25°C Note-1
Operating Temperature Range	T _{op}	-65 to +200	°С	Note § 2.
Storage Temperature Range	T _{stg}	-65 to +200	°C	Note 3, 2
Soldering Temperature For TO-18 For CCP	T _{sol}	+260 +245	°C	Note ¾ 3 Note § 4

NOTES:

For Tamb or T_{case} > +25°C, derate linearly to 0W-at +200°C.

-When mounted on a 15 x 15 x 0.6mm-ceramic substrate:

For Variants with tin-lead plating or hot solder dip lead finish all testing, and any handling, performed at T_{amb} > +125°C shall be carried out in a 100% inert atmosphere.

Duration 10 seconds maximum at a distance of not less than 1.5mm from the device body and the same lead shall not be resoldered until 3 minutes have elapsed.

Duration 5 seconds maximum and the same terminal shall not be resoldered until 3 minutes have elapsed.

Thermal Resistance, Junction - to - Ambient	Rth(j-a)	486	°c/w	
Thermal Resistance,				
Junction - to - Case	$R_{th(j-c)}$	145.8	°C/W	Note 1

—[1. Thermal Resistance, Junction-to-Case only applies to TO-18 packaged Variants.
Thermal Resistance, Junction-to-Soldering Point for Variants 06 and 07?



PAGE 12
ISSUE & 3 - Draft A

Characteristics	Symbols	MIL-STD-750	Test Conditions	Lir	nits	Units	
	Test Method			Min	Max		
Base-Emitter Saturation Voltage	V _{BE(sat)1}	3066	I _C =-10mA I _B =-1mA Note 1 Test condition A 2N2894 2N2894A	-780 -	-980 -	mV	
	V _{BE(sat)2}	3066	I _C =-30mA I _B =-3mA Note 1 Test condition A 2N2894 2N2894A	-0.85 -	-1.2 -1.15	V	
Magnitude of Small-Signal Short-Circuit Forward-Current Transfer Ratio	ih _{fe} l	3306	V _{CB} =-30mA, V _{CE} =-10V f=100MHz Note 2 2N2984 2N2894A	4 7	<u>-</u>	_	
Output Capacitance	C _{obo}	3236	V _{CB} =-5V, I _E =0A f=1MHz Note 2 2N2984 2N2894A	-	6 4.5	pF	
Input Capacitance	C _{ibo}	3240	V _{EB} =-500mV I _C =0A f=1MHz Note 2	-	6	pF	
Turn-on Time	t _{on}	-	V _{BB} =3V, V _{IN} =-7V, I _C =-30mA I _{BL} =1.5mA Notes 2, 3 2N2984 2N2894A	-	60 40	ns	
Turn-off Time	t _{off}	-	V _{BB} =-4V, V _{IN} =6V, I _C =-30mA I _{B1} =I _{B2} =1.5mA Notes 2, 3 2N2984 2N2894A	1	90 60	ns	

NOTES:

1. Pulse measurement: Pulse Width \leq 300 μ s, Duty Cycle \leq 2% .

2. For AC characteristics read and record measurements shall be performed on a sample of 32 components with 0 failures allowed. Alternatively a 100% inspection may be performed.

3. t_{on} shall be measured using the following test circuit. The input waveform shall be supplied by a pulse generator with the following characteristics: $Z_{OUT} = 50\Omega$, $t_r \le 2$ ns, Pulse Width = 200 ± 1 0ns, Duty Cycle ≤ 2 %. The output waveform shall be monitored on an oscilloscope with the following



2.4.2 <u>High and Low Temperatures Electrical Measurements</u>

Characteristics	Symbols	MIL-STD-750	Test Conditions	Limits		Units
		Test Method	Note 1	Min	Max	
Collector-Base Cut-off Current	I _{CBO}	3036	T _{amb} =+150 (+0 -5)°C V _{CB} =-50V Bias condition D	-	-10	μА
Forward-Current Transfer Ratio 2	h _{FE2}	3076 correct font	T _{amb} =-55 (+5 -0)°C V _{CE} =-500mV I _C =-30mA Note 2	20	-	-

NOTES:

1. Read and record measurements shall be performed on a sample of 5 components with 0 failures allowed. Alternatively a 100% inspection may be performed.

2. Pulsed measurement: Pulse Width ≤300µs, duty Cycle ≤2%.

2.5 PARAMETER DRIFT VALUES

Unless otherwise specified, the measurements shall be performed at T_{amb} =+22 $\pm 3^{o}C$.

The test methods and test conditions shall be as per the corresponding test defined in Room Temperature Electrical Measurements.

The drift values (Δ) shall not be exceeded for each characteristic specified. The corresponding absolute limit values for each characteristic shall not be exceeded.

Symbols	·	Limits		Units
	Drift	Abs	olute	
	Value Δ	Min	Max	
Ісво	±20 or (1) ±100%	-	-10	nA
h _{FE2}	±15%	40 40	150 150	-
V _{CE(sat)}	±50 or (1) ±15%	•	-500 -450	mV
	I _{CBO}	$\begin{array}{c c} & Drift \\ Value \\ \Delta \\ \\ I_{CBO} \\ & \pm 20 \\ or (1) \\ \pm 100\% \\ \\ h_{FE2} \\ & \pm 15\% \\ \\ \\ V_{CE(sat)} \\ & \pm 50 \\ or (1) \\ \end{array}$	Drift Value Δ Min	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$

NOTES:

1. Whichever is the greater referred to initial value.

PAGE 16

ISSUE \$ 3- Braff A

2.6 INTERMEDIATE AND END-POINT ELECTRICAL MEASUREMENTS

Unless otherwise specified, the measurements shall be performed at T_{amb} =+22 $\pm 3^{o}$ C.

The test methods and test conditions shall be as per the corresponding test defined in Room Temperature Electrical Measurements.

The limit values for each characteristic shall not be exceeded.

Characteristics	Symbols	Lir	Limits		
		Min	Max		
Collector-Base Cut-off Current	I _{CBO}	-	-100	nA	
Forward-Current Transfer Ratio 2 2N2894 2N2894A	h _{FE2}	40 40	150 150	-	
Collector-Emitter Saturation Voltage 3 2N2894 2N2894A	V _{CE(sat)}	-	-500 -450	mV	

2.7 HIGH TEMPERATURE REVERSE BIAS BURN-IN CONDITIONS

Characteristics	Symbols	Test Conditions	Units
Ambient Temperature	T _{amb}	+150 (+0 -5)	°C
Collector-Base Voltage	V _{CB}	12	V
Duration	t	72 minimum	Hours

2.8 **POWER BURN-IN CONDITIONS**

Characteristics	Symbols	Test Conditions	Units
Ambient Temperature	T _{amb} +20 to +50		°C
Power Dissipation	P _{tot}	As per Maximum Ratings. Ptot1 the material at the chosen Tamb Ms.'ng the	W
Collector-Base Voltage	V _{CB}	-10	V

OPERATING LIFE CONDITIONS

The conditions shall be as specified for Power Burn-in.

Specified Rth(j-a).

2.9